

# Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0035				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0042				
I <sub>D</sub> (A)	50				
Configuration	Single				

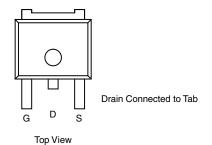
TO-252

### **FEATURES**

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified
- 100 % R<sub>g</sub> and UIS Tested
- Material categorization:
   For definitions of compliance please see www.freescale.net.cn

N-Channel MOSFET





ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD50N04-3m5L-GE3			

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	40	V
Gate-Source Voltage		$V_{GS}$	± 20	V
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	50	
	T <sub>C</sub> = 125 °C		50	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	50	Α
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	200	
Single Pulse Avalanche Current	1 0.1 ml l	I <sub>AS</sub>	55	
Single Pulse Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	151	mJ
Manifesture Bassas Biantinations	T <sub>C</sub> = 25 °C	D	136	W
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	45	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	50	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.1	G/VV	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).



## SQD50N04-3m5L Automotive N-Channel

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		-	2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	-	50	
		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$	-	-	150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	-	0.0029	0.0035	Ω
Drain-Source On-State Resistance <sup>a</sup>	D	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0056	
Dialii-Source Oil-State nesistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.0068	
		$V_{GS} = 4.5 \text{ V}$	I <sub>D</sub> = 20 A	-	0.0034	0.0042	
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		-	105	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>			-	4880	5860	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	560	670	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	250	300	
Total Gate Charge <sup>c</sup>	$Q_g$			-	85	130	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, I_D = 50 \text{ A}$	-	14	-	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	14	-	
Gate Resistance	$R_g$	f = 1 MHz		1	2	3	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	9	11	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 20 \text{ V}, \text{ R}_L = 0.4 \Omega$ $I_D \cong 50 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	11	14	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	39	47	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	11	14	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	200	Α
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0 V		-	0.9	1.5	V

#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



2000

1000

0

0

Coss

20

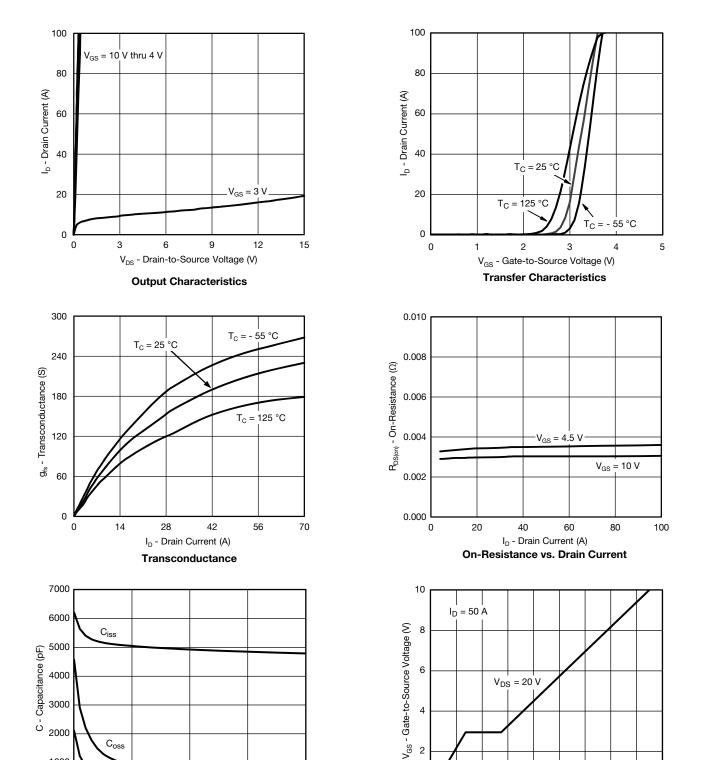
V<sub>DS</sub> - Drain-to-Source Voltage (V)

Capacitance

# SQD50N04-3m5L

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### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



4

2

0

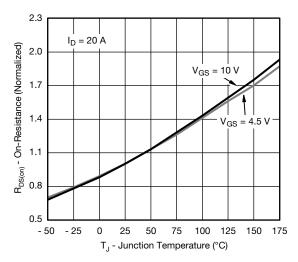
0

10 20 50

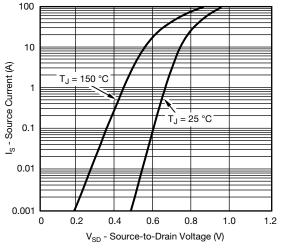
Q<sub>q</sub> - Total Gate Charge (nC) **Gate Charge** 

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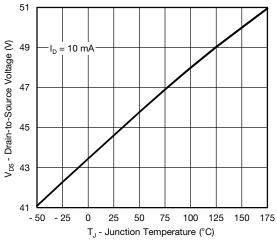
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



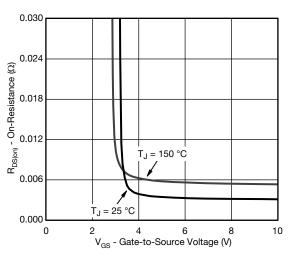
#### On-Resistance vs. Junction Temperature



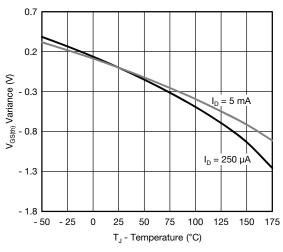
**Source Drain Diode Forward Voltage** 



Drain Source Breakdown vs. Junction Temperature



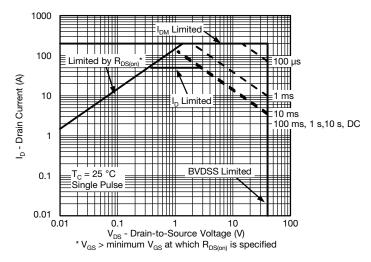
On-Resistance vs. Gate-to-Source Voltage



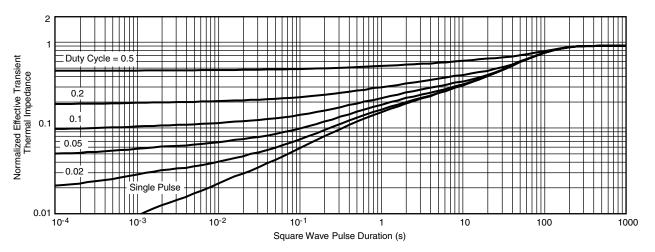
Threshold Voltage

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### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Safe Operating Area

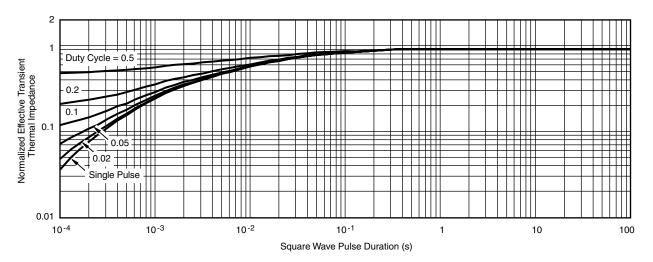


Normalized Thermal Transient Impedance, Junction-to-Ambient



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#### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

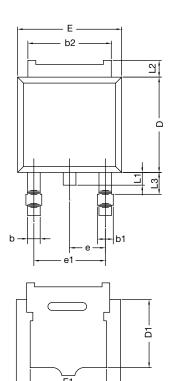
#### Note

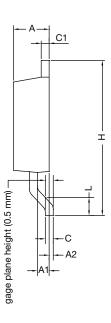
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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#### **TO-252AA CASE OUTLINE**





	MILLIMETERS		INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	BSC	0.090 BSC		
e1	4.57	BSC	0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

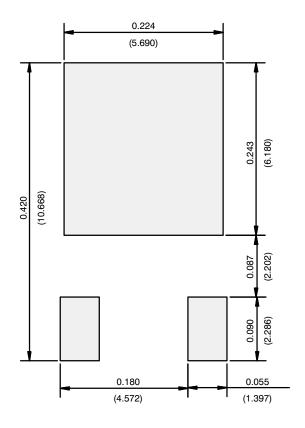
#### Note

• Dimension L3 is for reference only.

## SQD50N04-3m5L Automotive N-Channel

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#### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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### SQD50N04-3m5L Automotive N-Channel 30 V (D-S) 175 °C MOSFET

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